

ENHANCED PROTECTION FOR INPUT BUFFERS OF LOW-VOLTAGE FLASH MEMORIES

Abstract of the Disclosure

5 An input buffer is discussed that inhibits semiconductor breakdown of thin
gate-oxide transistors in low-voltage integrated circuits. One aspect of the input
buffer includes an input stage having a gate, a drain, and a source. The gate of the
input stage is receptive to an inhibiting signal, and the drain is receptive to an input
signal. The input stage inhibits the input signal from being presented at the source
10 of the input stage when the inhibiting signal is at a predetermined level. The input
buffer further includes an output stage having an inverter that includes a first
connection and a second connection. The first connection couples to the source of
the input stage, and the second connection presents the input signal to a low-voltage
flash memory device.

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